

ABSTRACT OF THE DISCLOSURE

A method for creating charged-particle-beam exposure data containing a description of an exposure sequence of character patterns to perform exposure of a charged-particle-beam according to a character projection technique, comprising selecting first or second values as a parameter to transfer one character pattern and then transferring a subsequent character pattern, the first value regarding performance of a shaping deflector which deflects the charged particle beam so that the charged particle beam is applied to an arbitrarily character aperture formed in a CP aperture mask and a character beam having the shape of the character aperture is thereby created, and the second value regarding performance of an objective deflector which deflects the character beam so that the character beam is applied to an arbitrarily position of the deflection region of the specimen, and determining the exposure sequence of the character patterns in the deflection region in accordance with the selected parameter.